

ABSTRACT OF THE DISCLOSURE

A method for seasoning a chamber and depositing a low dielectric constant layer on a substrate in the chamber is provided. In one aspect, the method includes seasoning the chamber with a first mixture comprising one or more organosilicon compounds and one or more oxidizing gases and depositing a low dielectric constant layer on a substrate in the chamber from a second mixture comprising one or more organosilicon compounds and one or more oxidizing gases, wherein a ratio of the total flow rate of the organosilicon compounds to the total flow rate of the oxidizing gases in the first mixture is lower than the total flow rate of the organosilicon compounds to the total flow rate of the oxidizing gases in the second mixture.